2SC5788

Silicon NPN epitaxial planar type

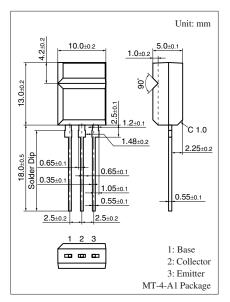
Power supply for Audio & Visual equipments such as TVs and VCRs Industrial equipments such as DC-DC converters

■ Features

- ullet High-speed switching (t_{stg} : storage time/ t_f : fall time is short)
- ullet Low collector to emitter saturation voltage $V_{CE(sat)}$
- Superior forward current transfer ratio hFE linearity
- Allowing automatic insertion with radial taping

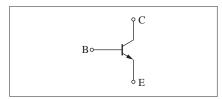
■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (En	V _{CBO}	60	V	
Collector-emitter voltage	V _{CEO}	60	V	
Emitter-base voltage (Collector open)		V _{EBO}	6	V
Collector current	I_{C}	3	A	
Peak collector current	I_{CP}	6	A	
Collector power	$T_C = 25^{\circ}C$	P _C	15	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		T _j	150	°C
Storage temperature		T _{stg}	−55 ~ +150	°C



Marking Symbol: C5788

Internal Connection



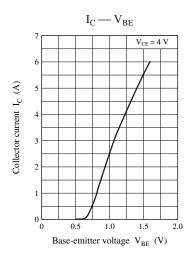
■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

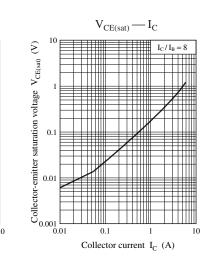
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 60 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 60 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 6 \text{ V}, I_C = 0$			1	mA
Forward current transfer ratio	h _{FE1} *	$V_{CE} = 4 \text{ V}, I_{C} = 1 \text{ A}$	120		320	_
	h _{FE2}	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$	40			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 3 \text{ A}, I_B = 375 \text{ mA}$			0.8	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 10 \text{ MHz}$		180		MHz
Turn-on time	t _{on}	I _C = 1 A, Resistance loaded		0.2	0.3	μs
Storage time	t _{stg}	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		0.55	0.7	μs
Fall time	$t_{\rm f}$	$V_{CC} = 50 \text{ V}$		0.1	0.15	μs

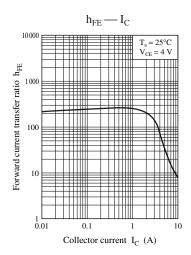
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

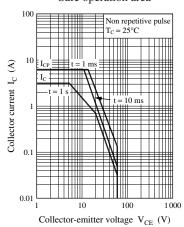
Rank	Р	Q			
$h_{\rm FE1}$	160 to 320	120 to 250			











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